

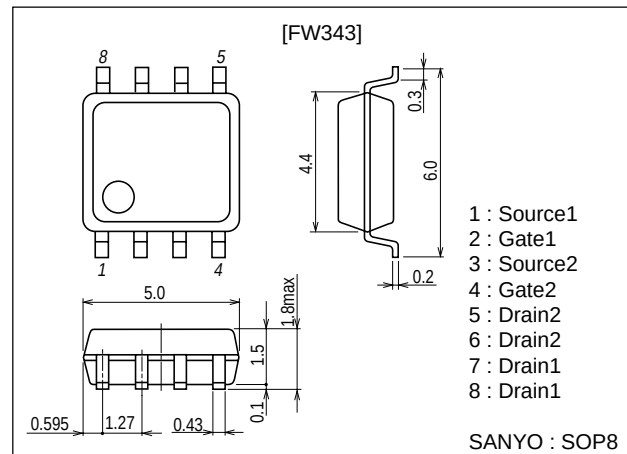
**FW343****Motor Driver Applications****Features**

- Low ON-resistance.
- Ultrahigh-speed switching.
- Composite type with an N-channel MOSFET and a P-channel MOSFET driving from a 4V supply voltage contained in a single package.
- High-density mounting.

Package Dimensions

unit : mm

2129

**Specifications****Absolute Maximum Ratings** at Ta=25°C

Parameter	Symbol	Conditions	Ratings		Unit
			N-channel	P-channel	
Drain-to-Source Voltage	V_{DSS}		30	-30	V
Gate-to-Source Voltage	V_{GSS}		±20	±20	V
Drain Current (DC)	I_D		5	-4	A
Drain Current (PW≤10s)	I_D	duty cycle≤1%	5.5	-4.5	A
Drain Current (PW≤100ms)	I_D	duty cycle≤1%	7	-6.5	A
Drain Current (PW≤10μs)	I_{DP}	duty cycle≤1%	20	-16	A
Allowable Power Dissipation	P_D	Mounted on a ceramic board (2000mm²×0.8mm)1unit, PW≤10s	1.8		W
Total Dissipation	P_T	Mounted on a ceramic board (2000mm²×0.8mm),PW≤10s	2.2		W
Channel Temperature	T_{ch}		150		°C
Storage Temperature	T_{stg}		-55 to +150		°C

Electrical Characteristics at Ta=25°C

Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	
[N-channel]						
Drain-to-Source Breakdown Voltage	V(BR)DSS	ID=1mA, VGS=0	30			V
Zero-Gate Voltage Drain Current	IDSS	VDS=30V, VGS=0			1	μA
Gate-to-Source Leakage Current	IGSS	VGS=±16V, VDS=0			±10	μA
Cutoff Voltage	VGS(off)	VDS=10V, ID=1mA	1.2		2.6	V

Marking : W343

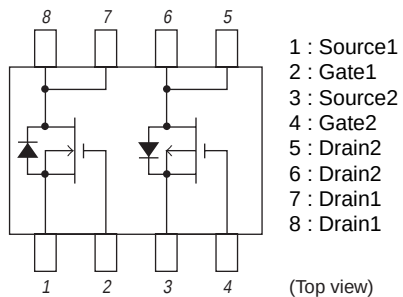
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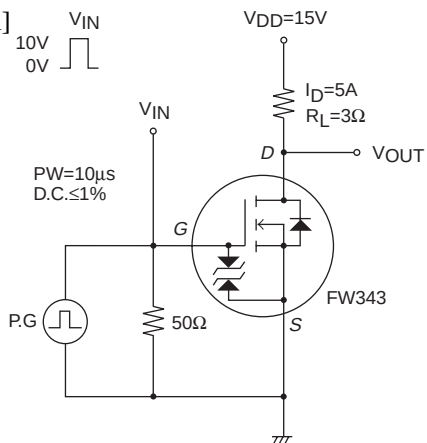
Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	
Forward Transfer Admittance	$ y_{fs} $	$V_{DS}=10V, I_D=5A$	3.9	5.5		S
Static Drain-to-Source On-State Resistance	$R_{DS(on)1}$	$I_D=5A, V_{GS}=10V$		37	48	$m\Omega$
	$R_{DS(on)2}$	$I_D=3A, V_{GS}=4V$		64	83	$m\Omega$
Input Capacitance	C_{iss}	$V_{DS}=10V, f=1MHz$		460		pF
Output Capacitance	C_{oss}	$V_{DS}=10V, f=1MHz$		95		pF
Reverse Transfer Capacitance	C_{rss}	$V_{DS}=10V, f=1MHz$		75		pF
Turn-ON Delay Time	$t_d(on)$	See specified Test Circuit.		11		ns
Rise Time	t_r	See specified Test Circuit.		20		ns
Turn-OFF Delay Time	$t_d(off)$	See specified Test Circuit.		30		ns
Fall Time	t_f	See specified Test Circuit.		20		ns
Total Gate Charge	Q_g	$V_{DS}=10V, V_{GS}=10V, I_D=5A$		8.6		nC
Gate-to-Source Charge	Q_{gs}	$V_{DS}=10V, V_{GS}=10V, I_D=5A$		2.0		nC
Gate-to-Drain "Miller" Charge	Q_{gd}	$V_{DS}=10V, V_{GS}=10V, I_D=5A$		1.6		nC
Diode Forward Voltage	V_{SD}	$I_S=5A, V_{GS}=0$		0.9	1.2	V
[P-channel]						
Drain-to-Source Breakdown Voltage	$V_{(BR)DSS}$	$I_D=-1mA, V_{GS}=0$	-30			V
Zero-Gate Voltage Drain Current	I_{DSS}	$V_{DS}=-30V, V_{GS}=0$			-1	μA
Gate-to-Source Leakage Current	I_{GSS}	$V_{GS}=\pm 16V, V_{DS}=0$			± 10	μA
Cutoff Voltage	$V_{GS(off)}$	$V_{DS}=-10V, I_D=-1mA$	-1.2		-2.3	V
Forward Transfer Admittance	$ y_{fs} $	$V_{DS}=-10V, I_D=-4A$	3.5	5		S
Static Drain-to-Source On-State Resistance	$R_{DS(on)1}$	$I_D=-4A, V_{GS}=-10V$		53	69	$m\Omega$
	$R_{DS(on)2}$	$I_D=-2A, V_{GS}=-4V$		105	147	$m\Omega$
Input Capacitance	C_{iss}	$V_{DS}=-10V, f=1MHz$		510		pF
Output Capacitance	C_{oss}	$V_{DS}=-10V, f=1MHz$		115		pF
Reverse Transfer Capacitance	C_{rss}	$V_{DS}=-10V, f=1MHz$		78		pF
Turn-ON Delay Time	$t_d(on)$	See specified Test Circuit.		11		ns
Rise Time	t_r	See specified Test Circuit.		55		ns
Turn-OFF Delay Time	$t_d(off)$	See specified Test Circuit.		35		ns
Fall Time	t_f	See specified Test Circuit.		40		ns
Total Gate Charge	Q_g	$V_{DS}=-10V, V_{GS}=-10V, I_D=-4A$		11		nC
Gate-to-Source Charge	Q_{gs}	$V_{DS}=-10V, V_{GS}=-10V, I_D=-4A$		2.4		nC
Gate-to-Drain "Miller" Charge	Q_{gd}	$V_{DS}=-10V, V_{GS}=-10V, I_D=-4A$		1.7		nC
Diode Forward Voltage	V_{SD}	$I_S=-4A, V_{GS}=0$		-0.9	-1.5	V

Electrical Connection

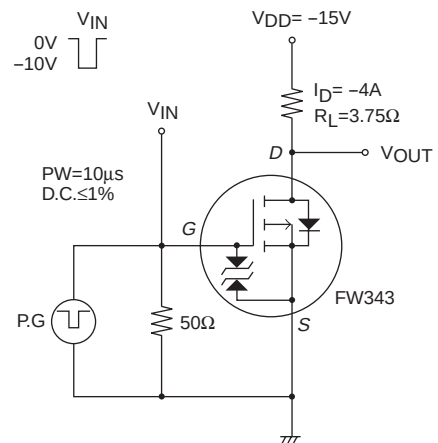


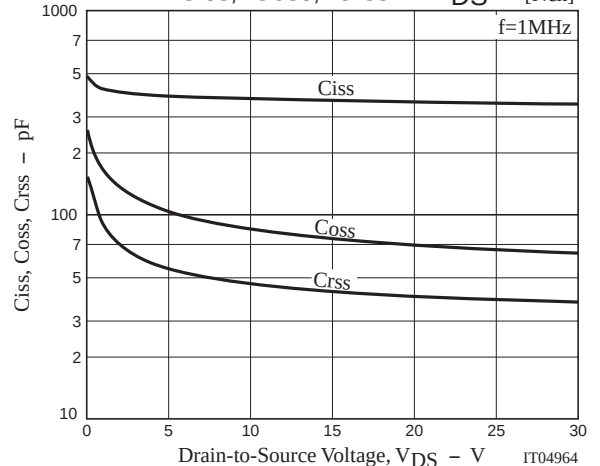
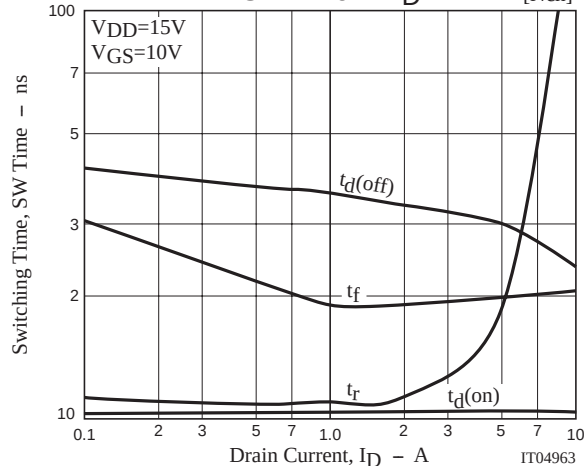
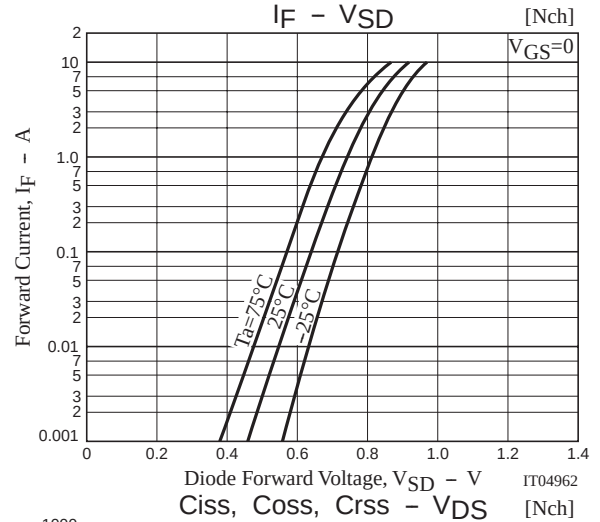
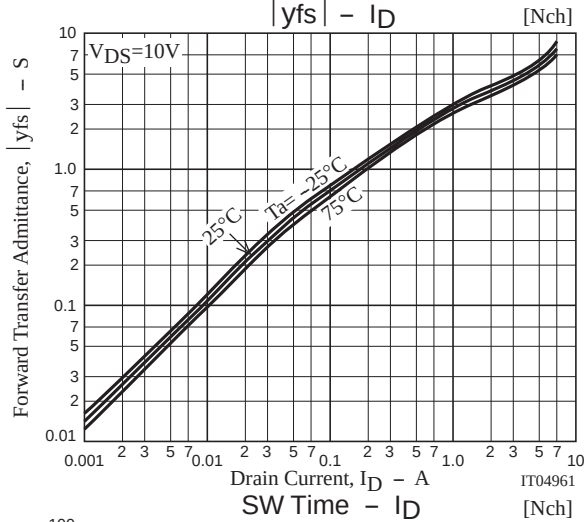
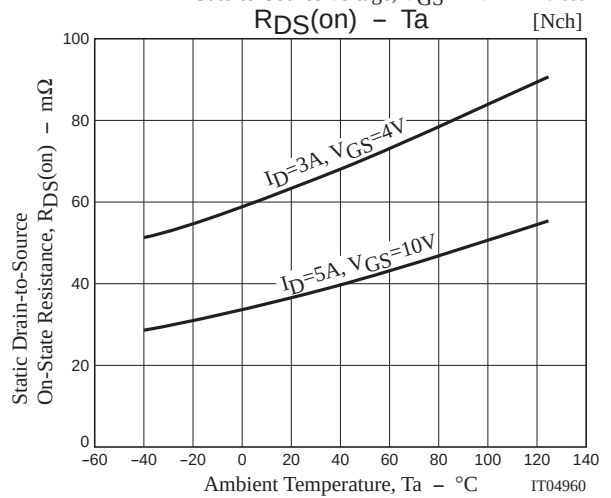
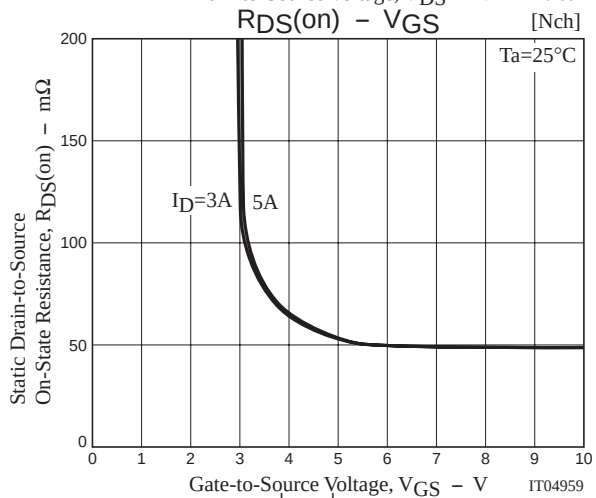
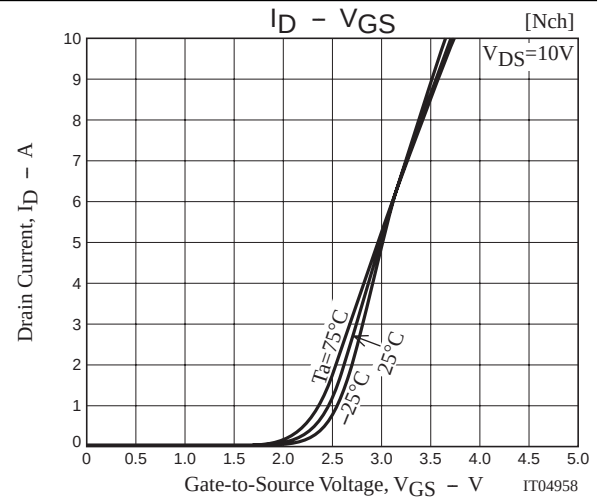
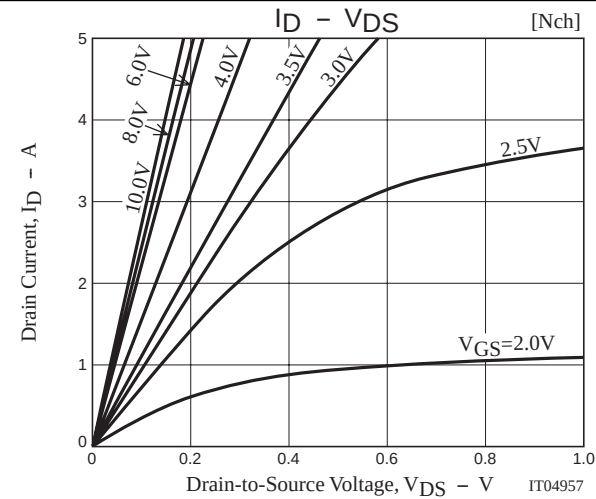
Switching Time Test Circuit

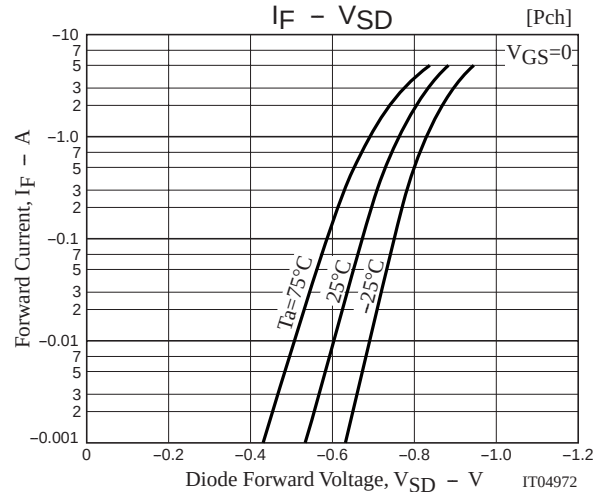
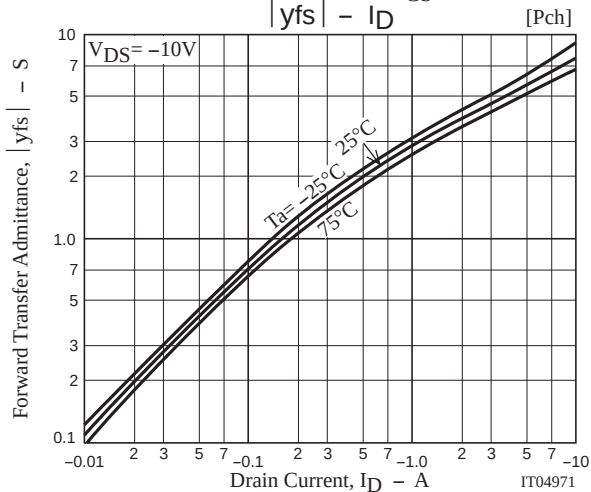
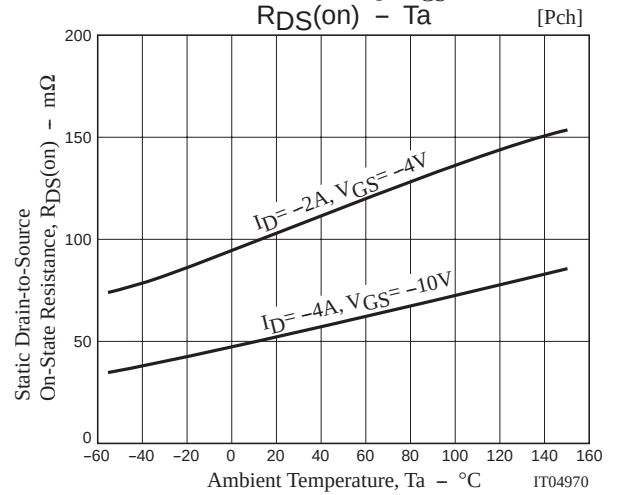
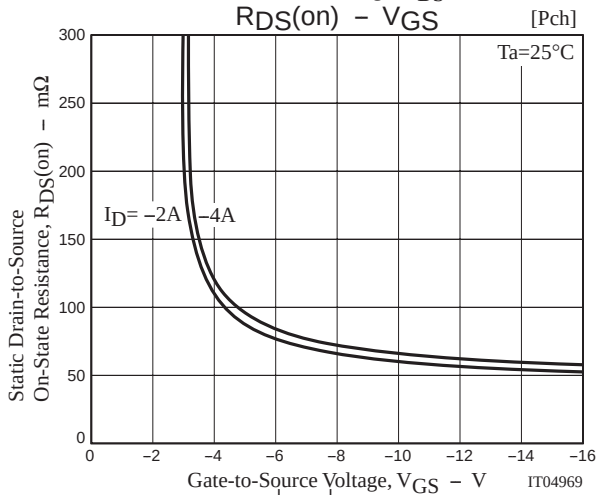
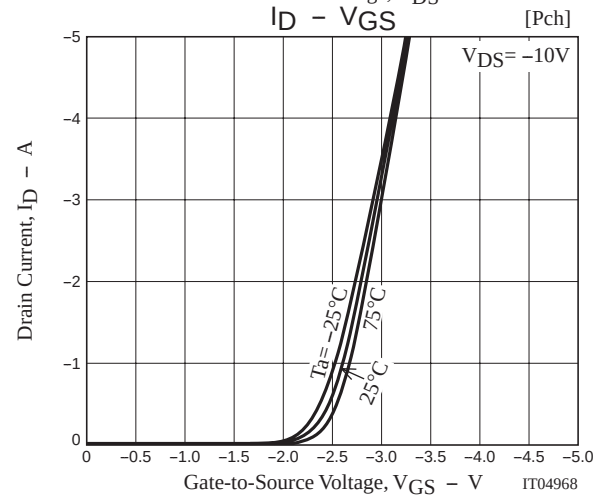
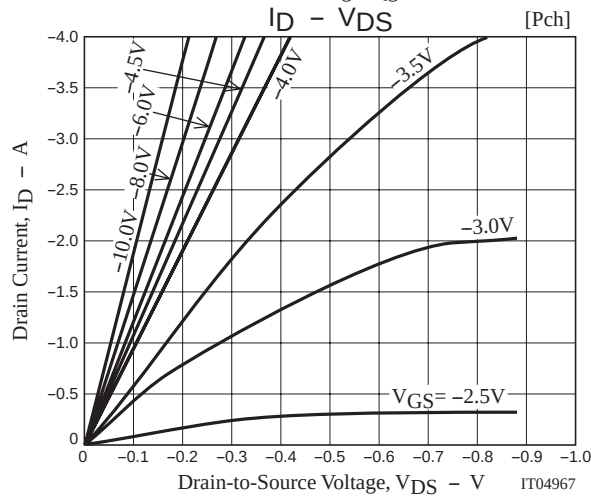
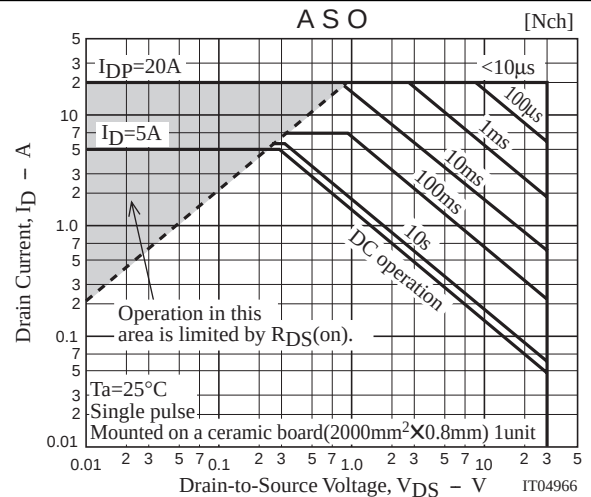
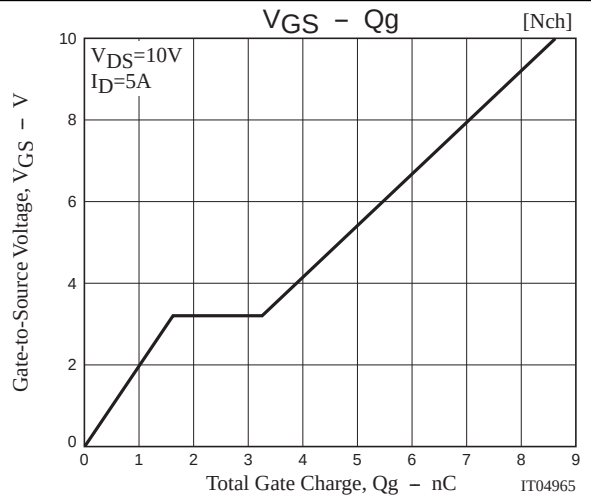
[N-channel]

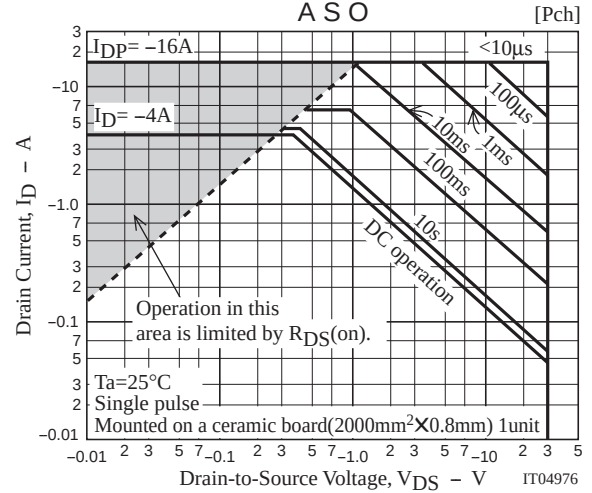
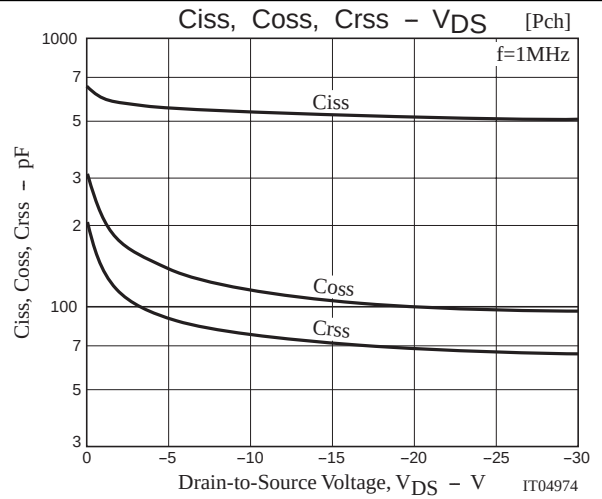
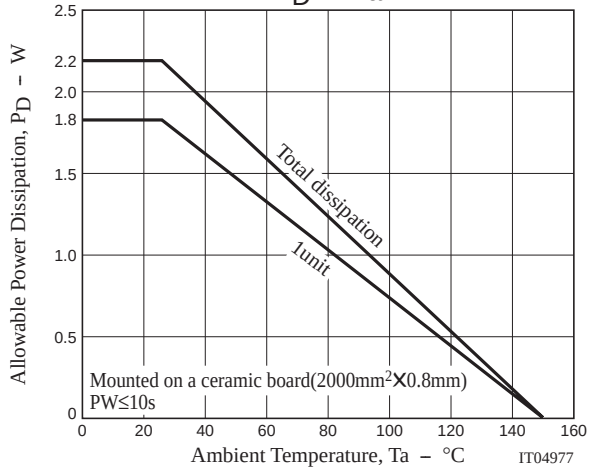
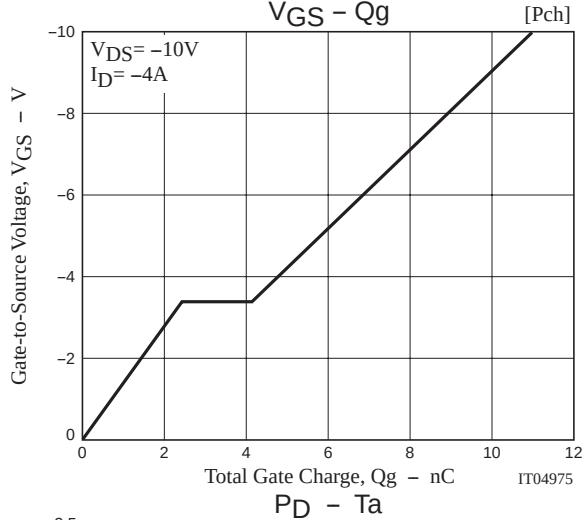
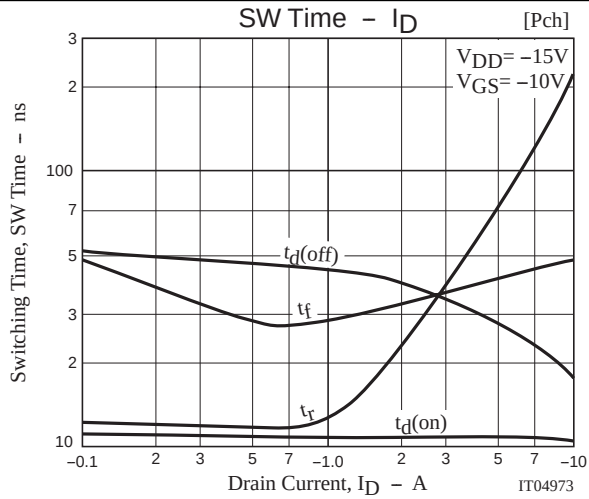


[P-channel]









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